


National Centre For Photovoltaic Research and Education			
	Process Details and Quality Parameters (Prepared by)	Doc. NO.	NCPRE 1
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Process	Edge Isolation Process
Objectives	Eliminate shunting from Top to Bottom of a Solar Cell
Outcome of process	Shunt Elimination resulting in Isolation of top and bottom of solar cell
Process in Detail	<ul style="list-style-type: none"> • SF₆ gas is used for etching silicon. It results in higher etch rates as compared to CF₄ • A higher RF power ~ 150 W is used • Maximum gas flow of 27 sccm is used to ensure faster etching • It is always advisable to do over etching.
Critical to Process	Process Time, Process gas
Measurable of the process quality	Shunt Resistance
Any other	
References (if any)	

NOTE:

- The whole idea of writing this process flow is to provide the process details in fine manner so that anybody else can repeat the process without your help.
- The process parameter may get modified over period of time, which we can be incorporated in the process later.
- Provide details of process. If required, very brief description of aspects of process can be added